Digital Integrated Circuits

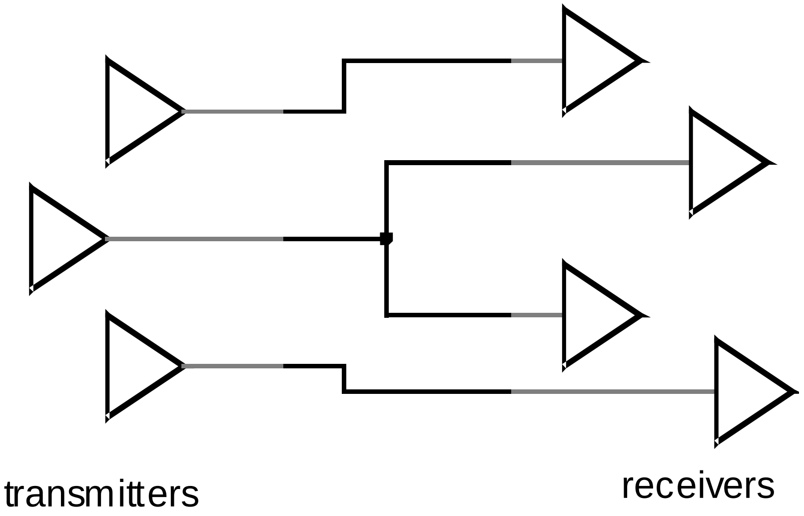
A Design Perspective

Jan M. Rabaey
Anantha Chandrakasan
Borivoje Nikolic

The Wire

July 30, 2002

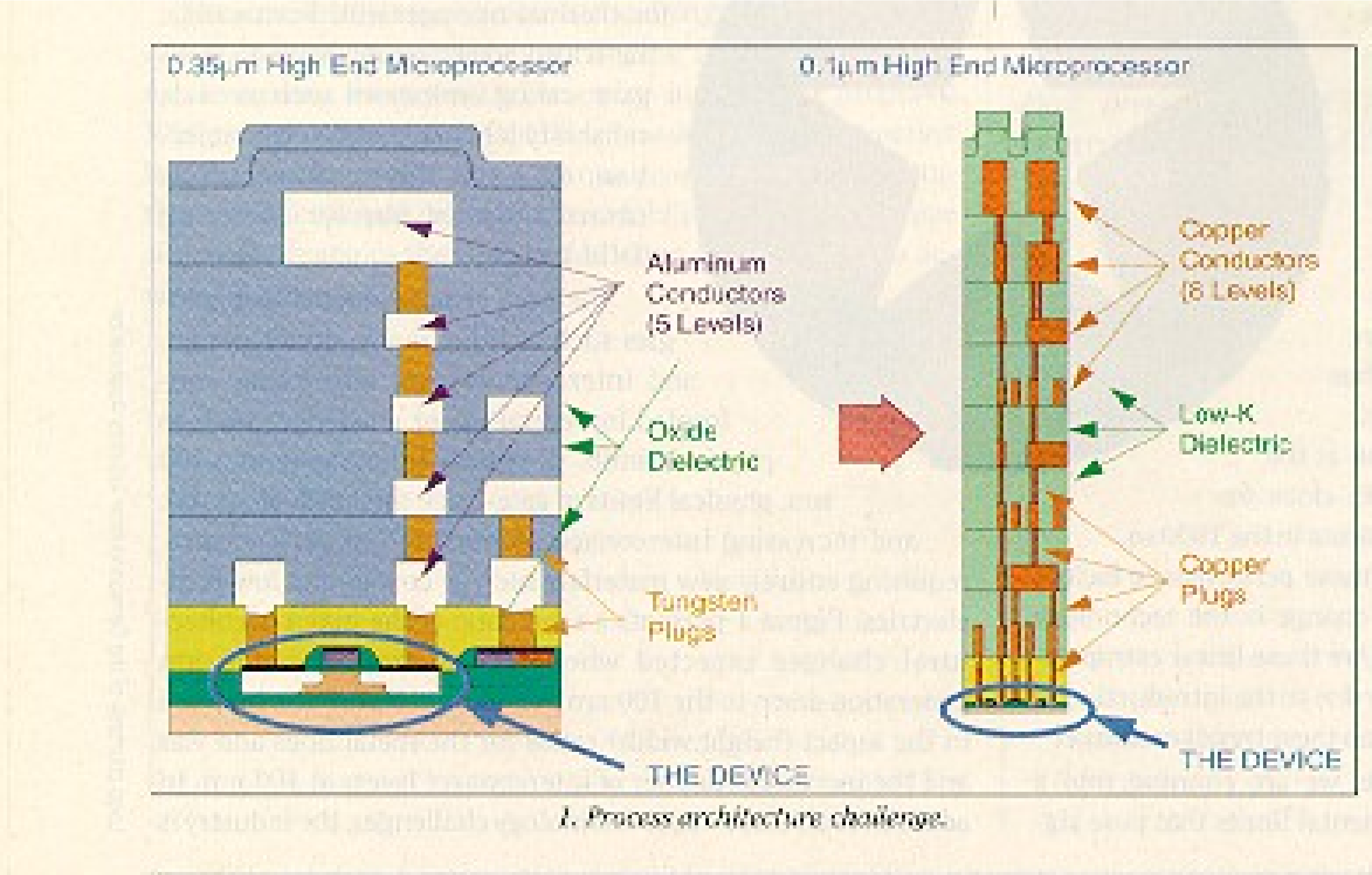
The Wire



schematics

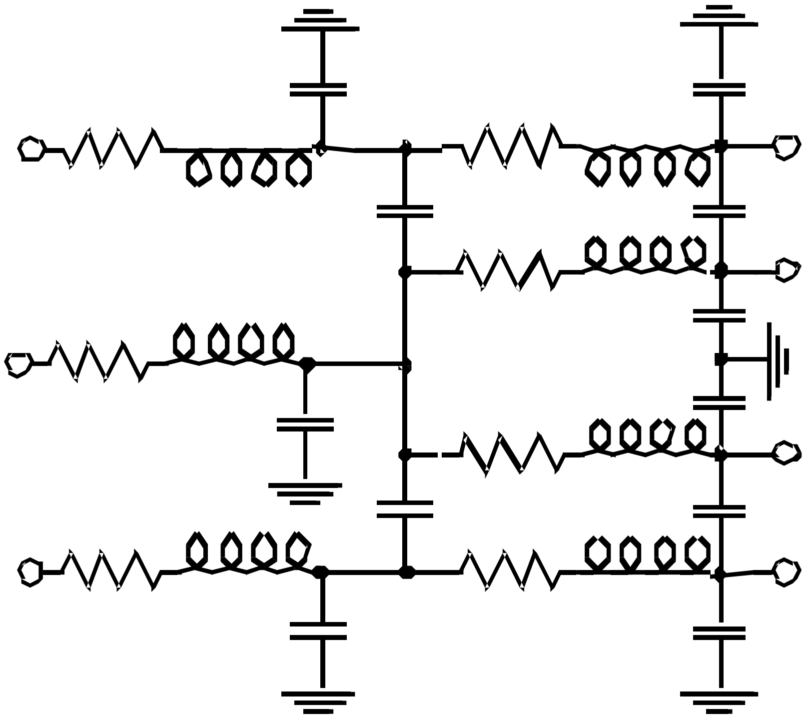
physical

Interconnect Impact on Chip

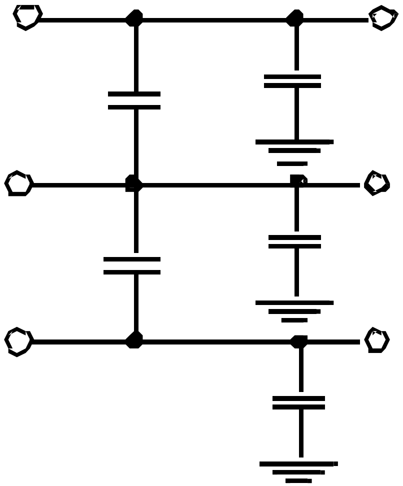


1. Process architecture challenge.

Wire Models



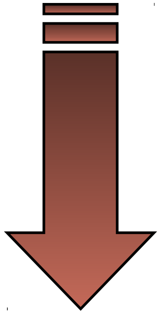
All-inclusive model



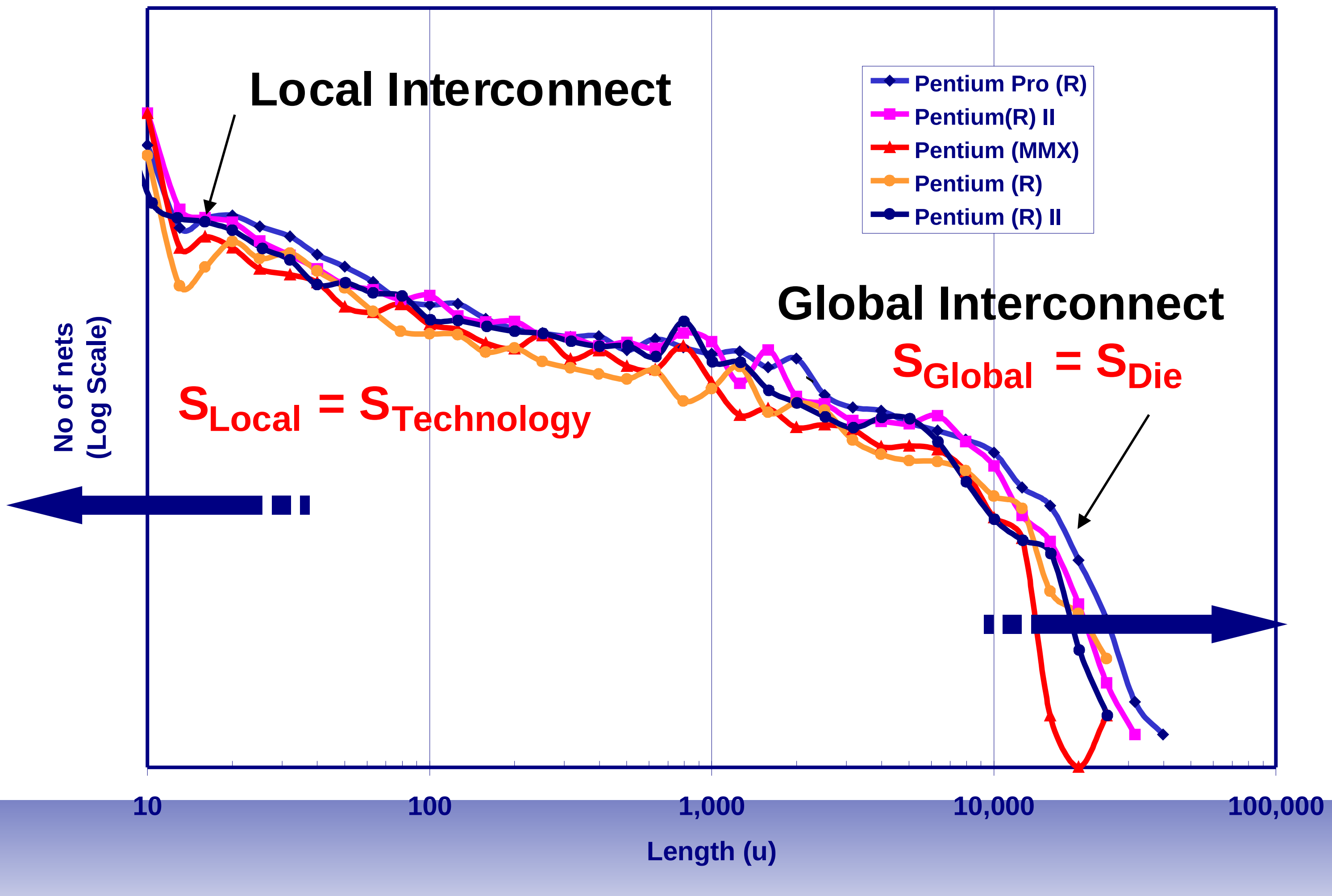
Capacitance-only

Impact of Interconnect Parasitics

- Interconnect parasitics
  - reduce reliability
  - affect performance and power consumption
- Classes of parasitics
  - Capacitive
  - Resistive
  - Inductive



Nature of Interconnect

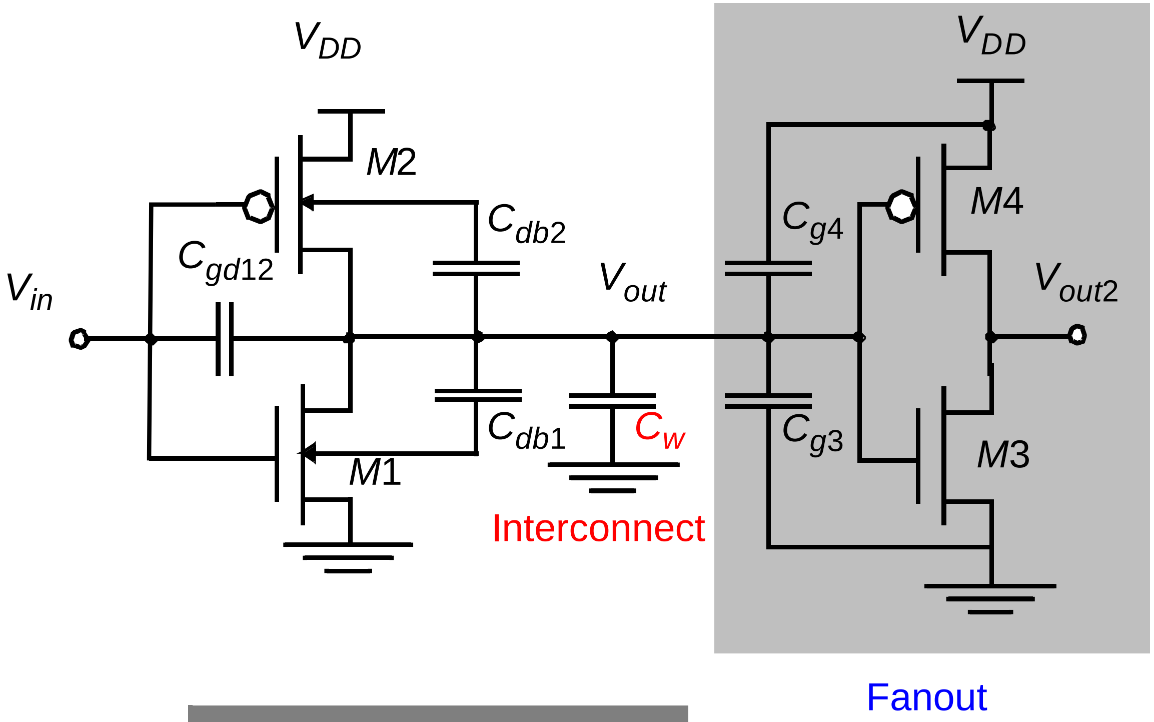


Source: Intel

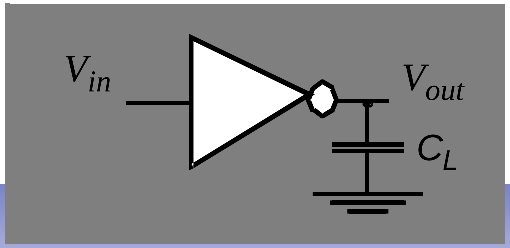
INTERCONNECT

Capacitance

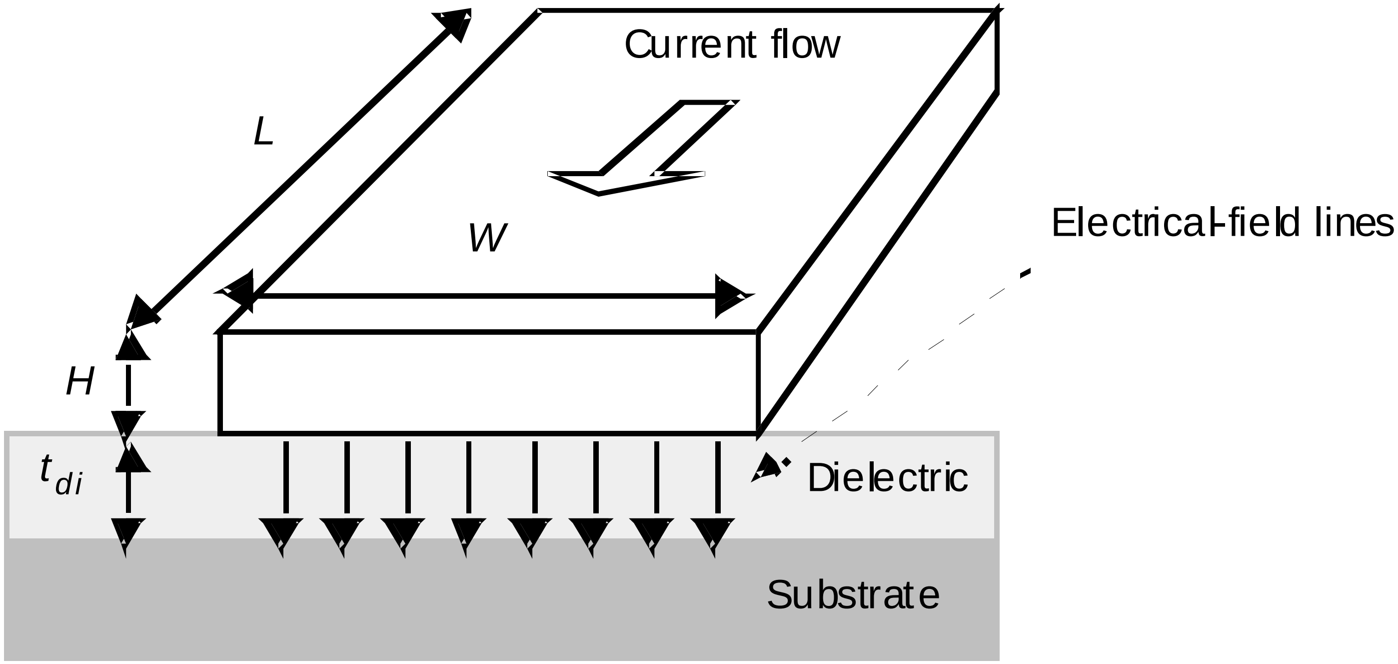
Capacitance of Wire Interconnect



Simplified Model



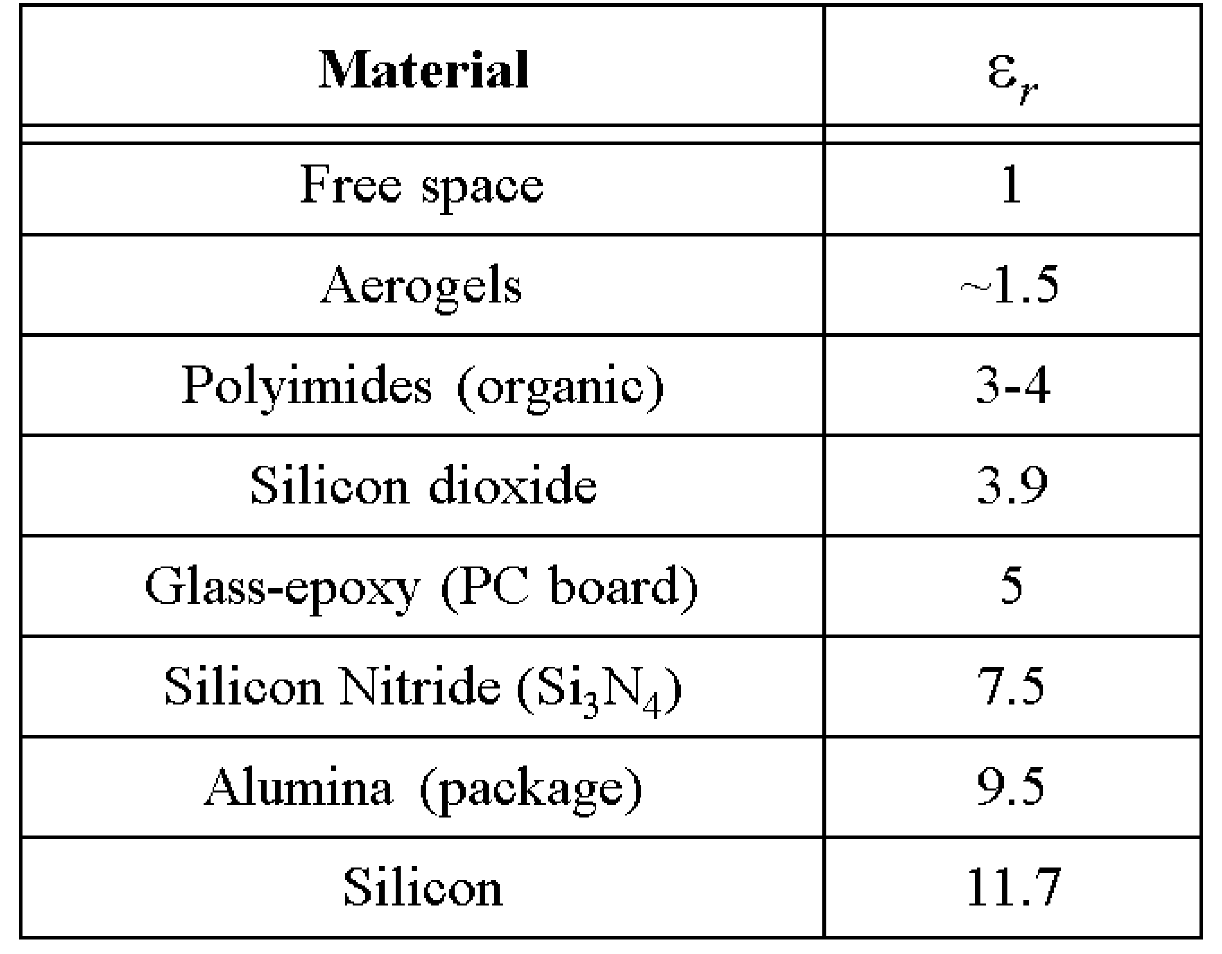
Capacitance: The Parallel Plate Model



$$c_{int} = \frac{\varepsilon_{di}}{t_{di}} WL$$

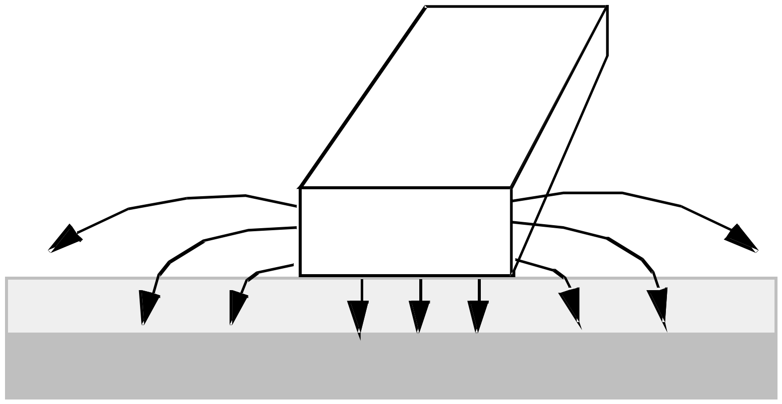
$$S_{Cwire} = \frac{S}{S \cdot S_L} = \frac{1}{S_L}$$

Permittivity



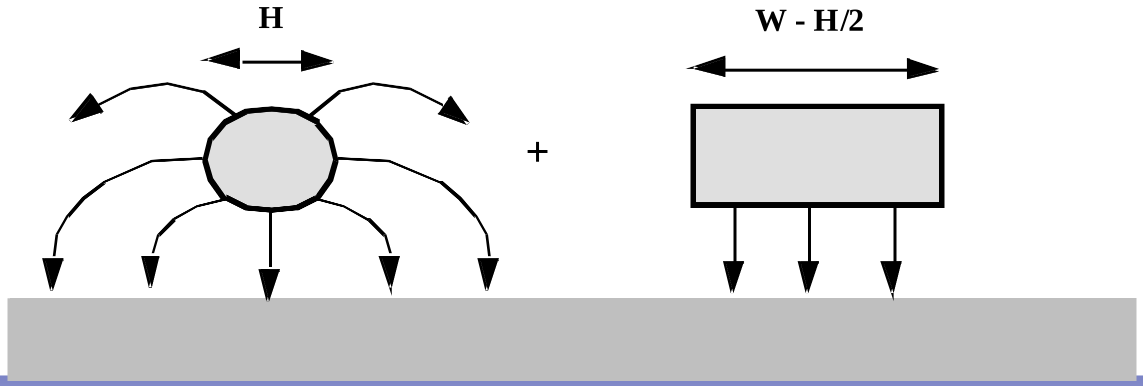
Material	ε_r
Free space	1
Aerogels	~1.5
Polyimides (organic)	3-4
Silicon dioxide	3.9
Glass-epoxy (PC board)	5
Silicon Nitride (Si_3N_4)	7.5
Alumina (package)	9.5
Silicon	11.7

Fringing Capacitance



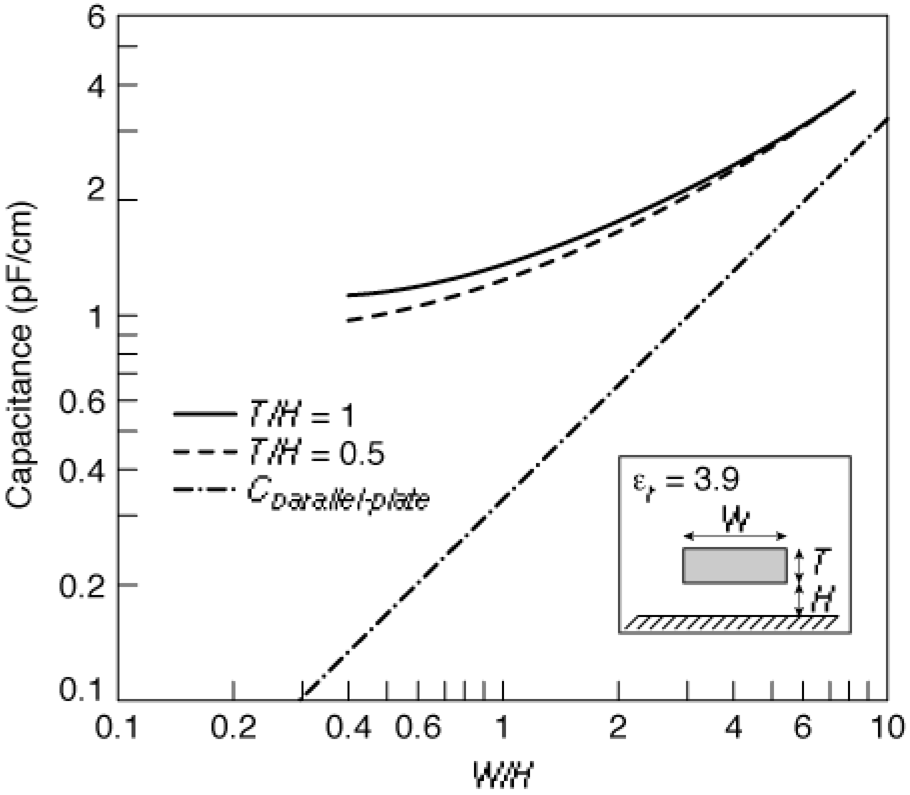
(a)

$$c_{wire} = c_{pp} + c_{fringe} = \frac{w\varepsilon_{di}}{t_{di}} + \frac{2\pi\varepsilon_{di}}{\log(t_{di}/H)}$$



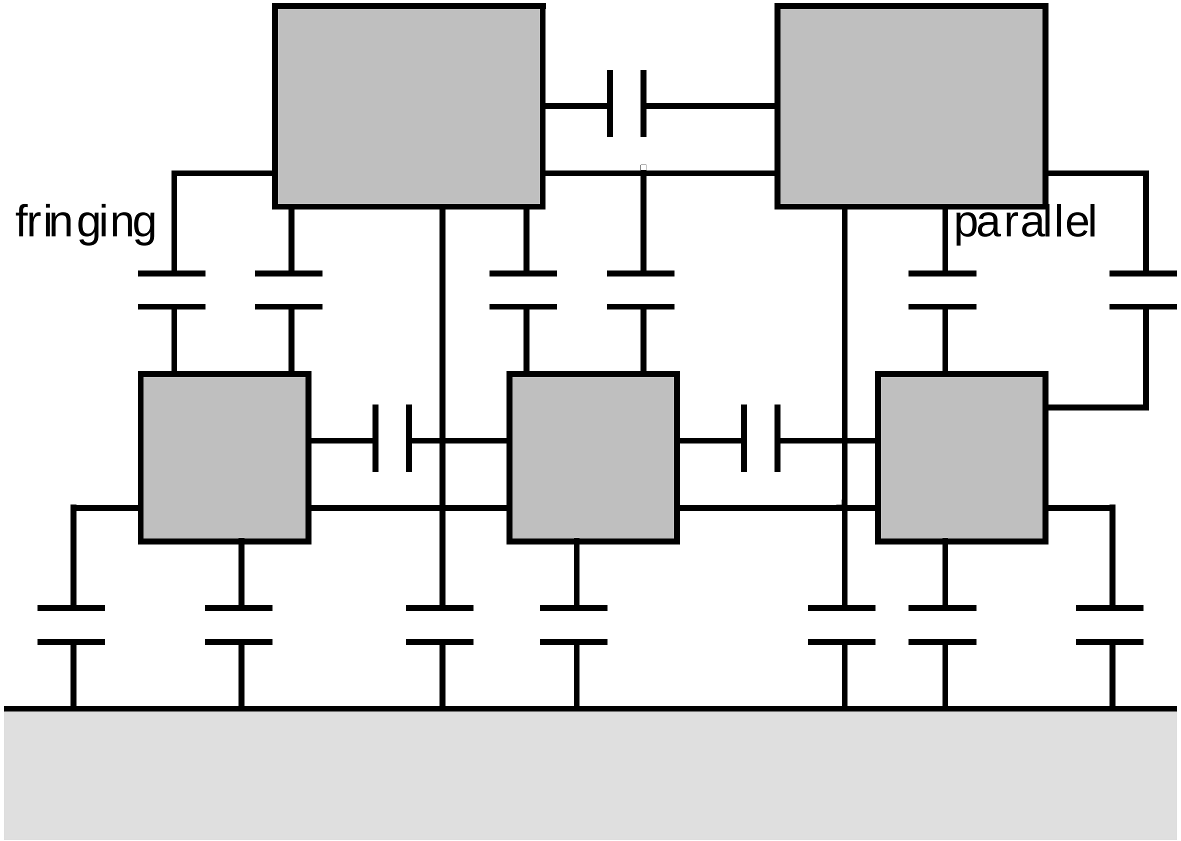
(b)

Fringing versus Parallel Plate

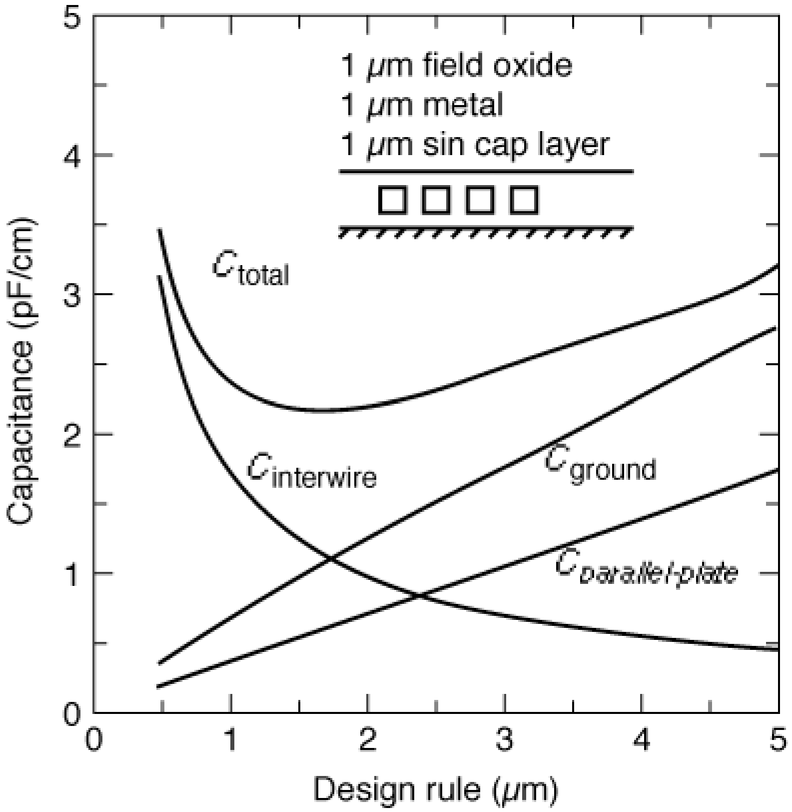


(from [Bakoglu89])

Interwire Capacitance

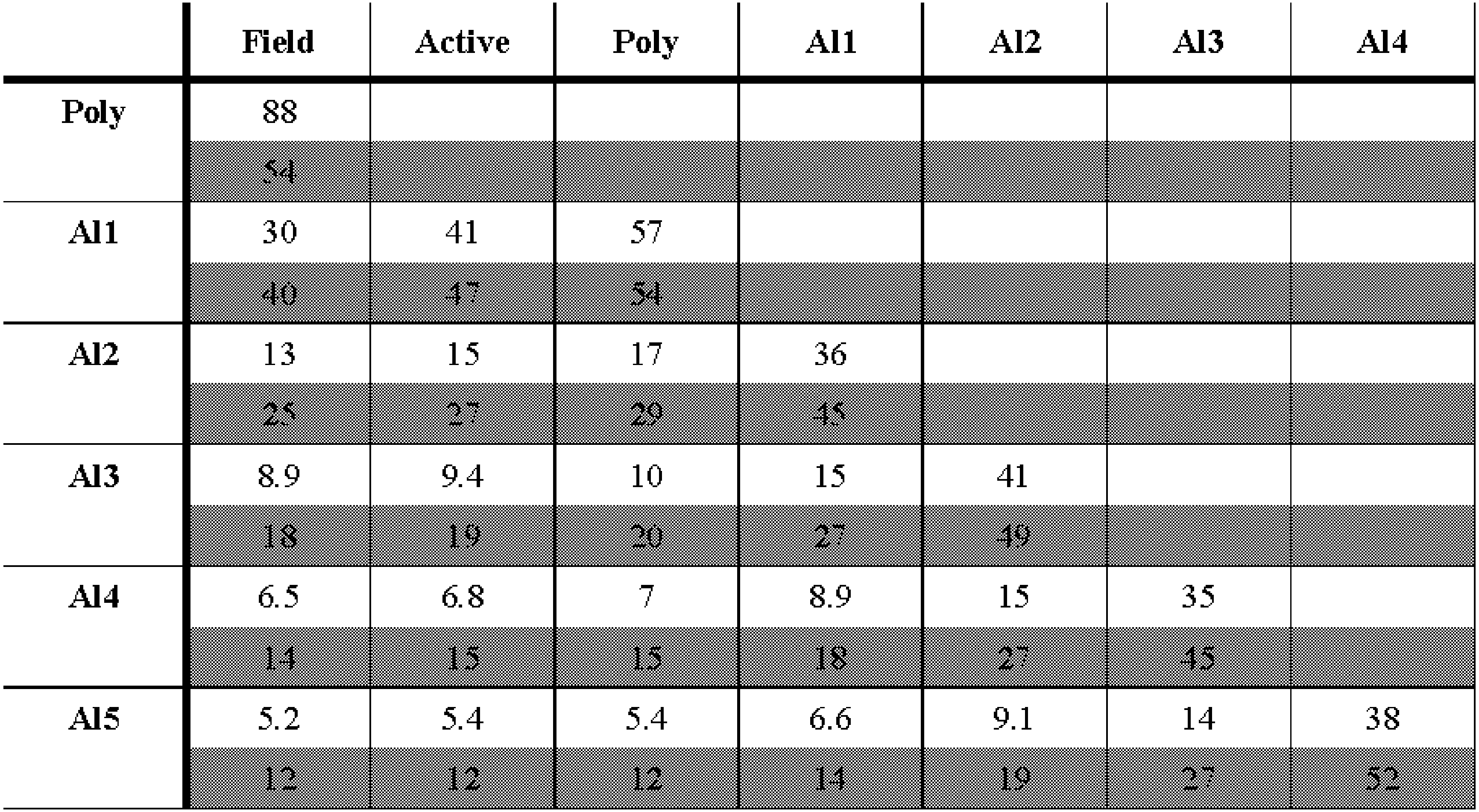


Impact of Interwire Capacitance



(from [Bakoglu89])

Wiring Capacitances (0.25 μm CMOS)

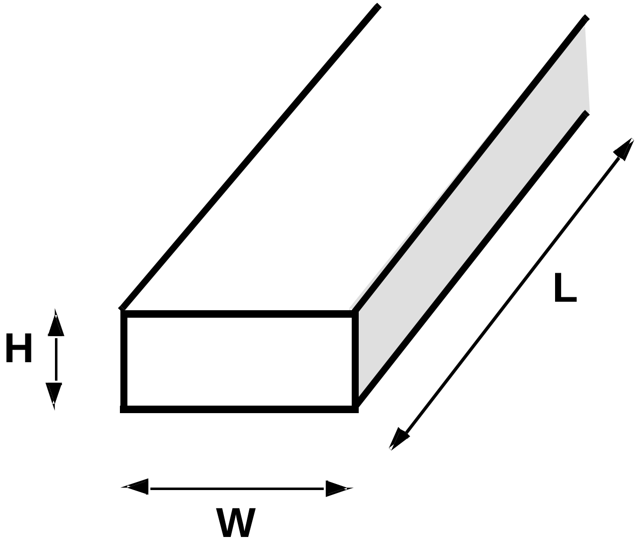


	Field	Active	Poly	Al1	Al2	Al3	Al4
Poly	88						
	54						
Al1	30	41	57				
	40	47	54				
Al2	13	15	17	36			
	25	27	29	45			
Al3	8.9	9.4	10	15	41		
	18	19	20	27	49		
Al4	6.5	6.8	7	8.9	15	35	
	14	15	15	18	27	45	
Al5	5.2	5.4	5.4	6.6	9.1	14	38
	12	12	12	14	19	27	52

INTERCONNECT

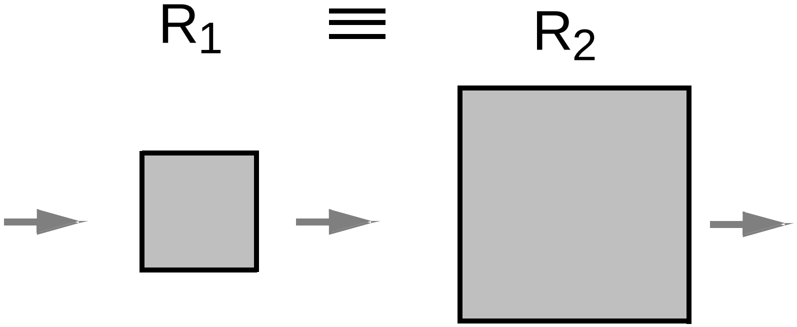
Resistance

Wire Resistance



$$R = \frac{\rho \, L}{H \, W}$$

Sheet Resistance
R_o



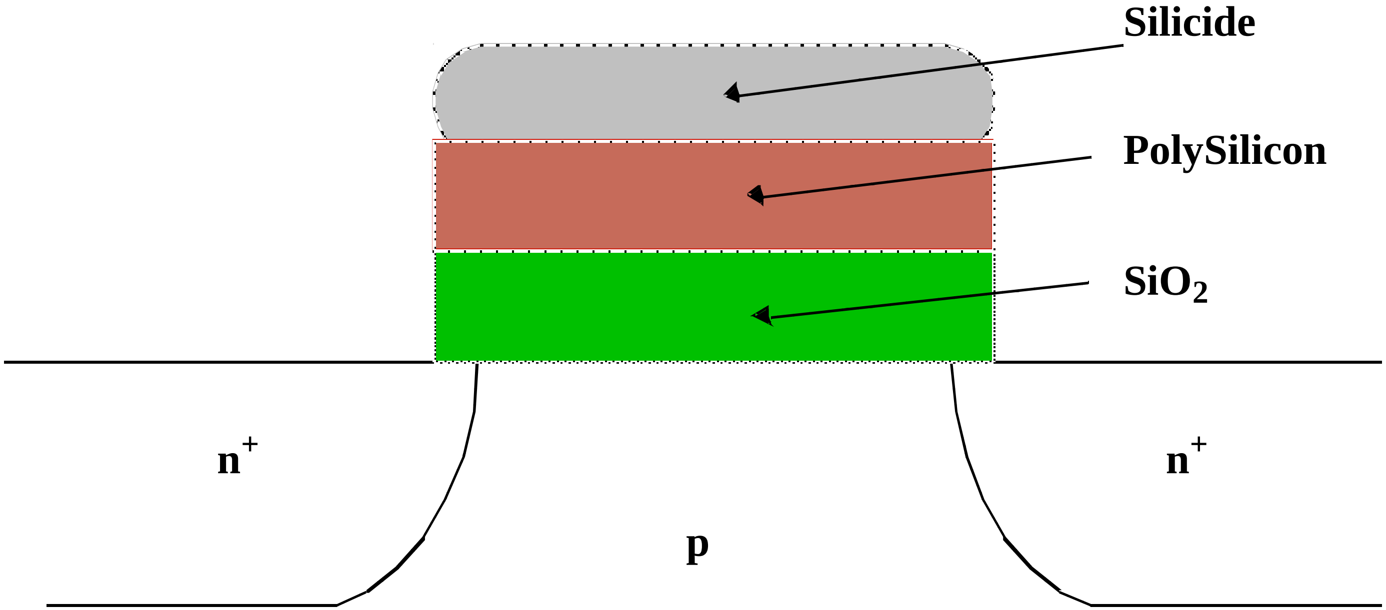
Interconnect Resistance

Material	**ρ (Ω-m)**
Silver (Ag)	1.6×10^{-8}
Copper (Cu)	1.7×10^{-8}
Gold (Au)	2.2×10^{-8}
Aluminum (Al)	2.7×10^{-8}
Tungsten (W)	5.5×10^{-8}

Dealing with Resistance

- **Selective Technology Scaling**
- **Use Better Interconnect Materials**
  - reduce average wire-length
  - e.g. copper, silicides
- **More Interconnect Layers**
  - reduce average wire-length

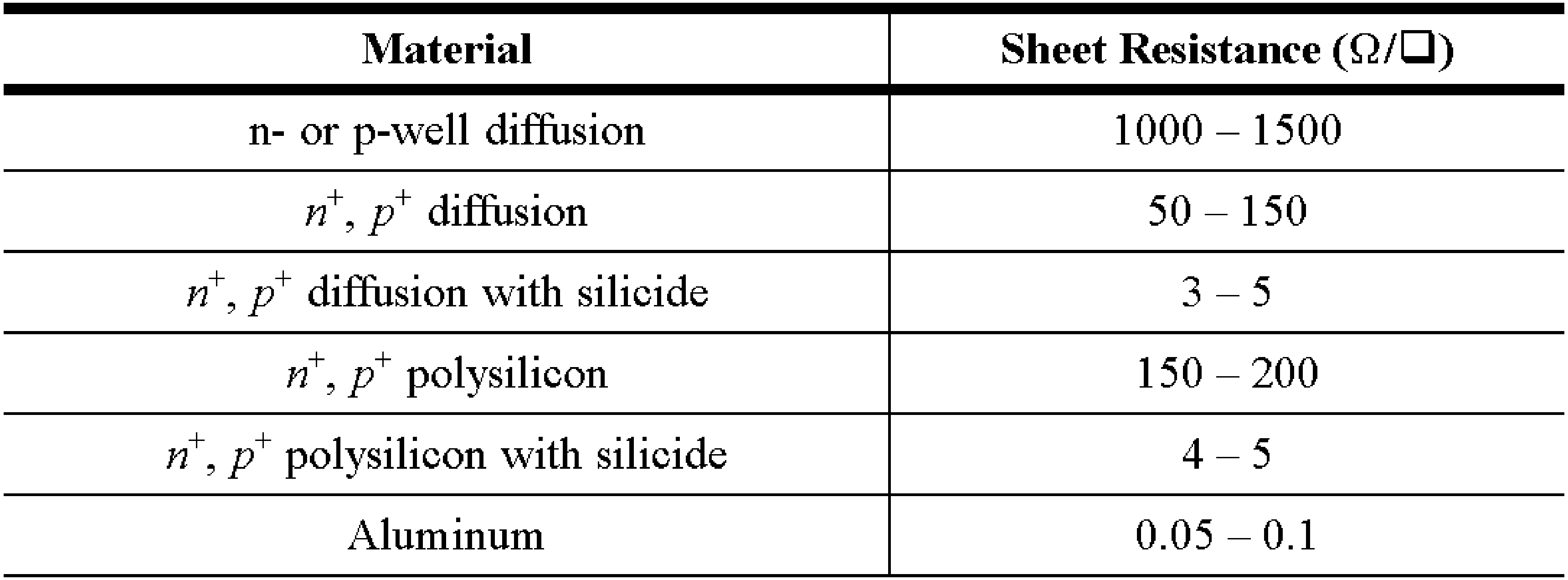
Polycide Gate MOSFET



Silicides: WSi_2, $TiSi_2$, $PtSi_2$ and TaSi

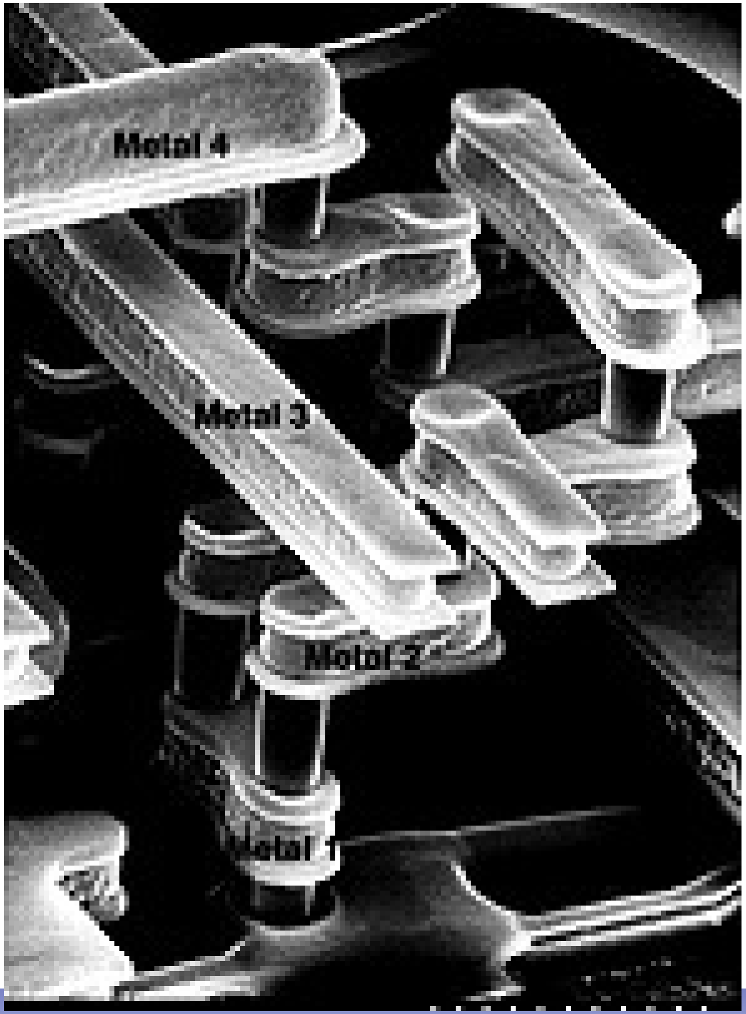
Conductivity: 8-10 times better than Poly

Sheet Resistance



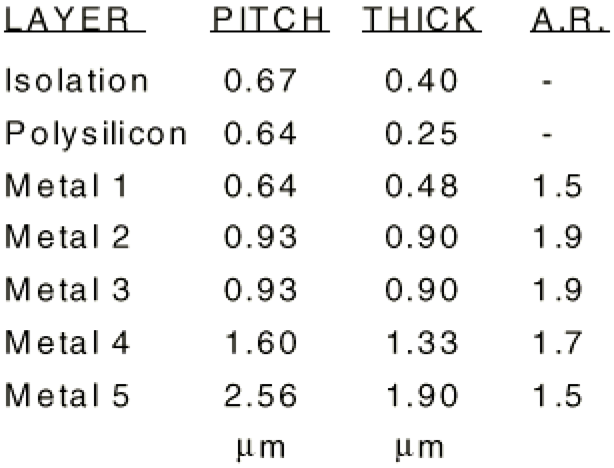
Material	Sheet Resistance (Ω/□)
n- or p-well diffusion	1000 – 1500
n^+, p^+ diffusion	50 – 150
n^+, p^+ diffusion with silicide	3 – 5
n^+, p^+ polysilicon	150 – 200
n^+, p^+ polysilicon with silicide	4 – 5
Aluminum	0.05 – 0.1

Modern Interconnect



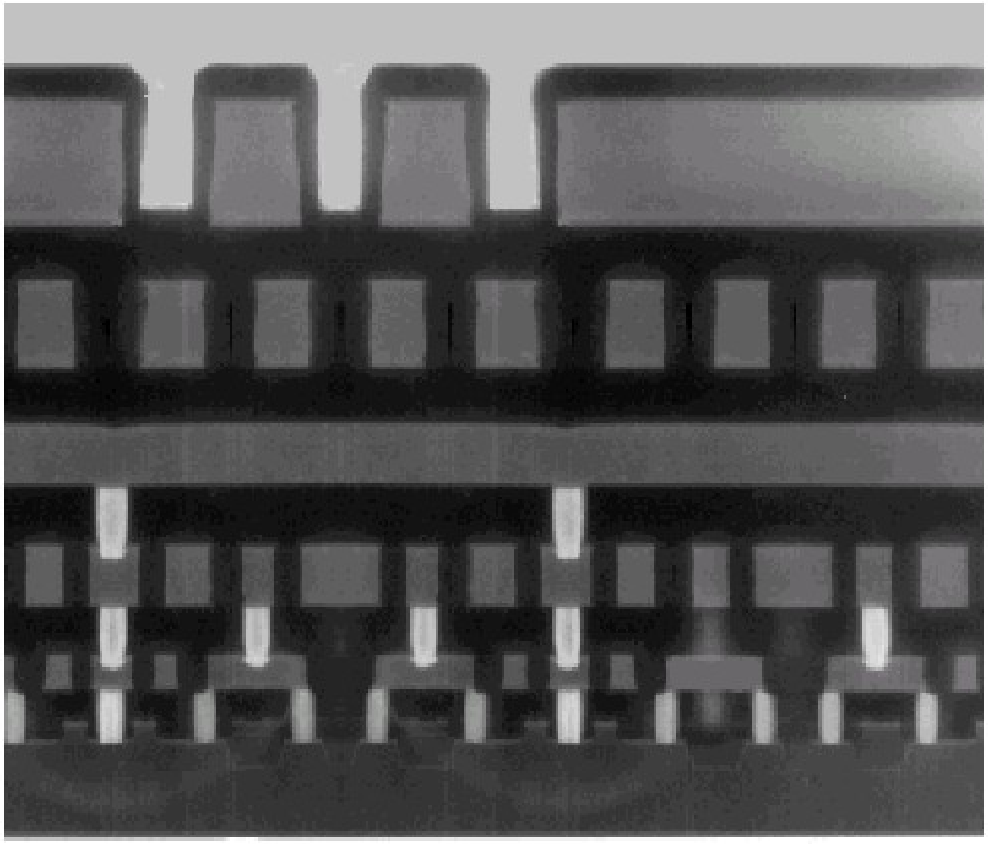
Example: Intel 0.25 micron Process

5 metal layers
Ti/Al - Cu/Ti/TiN
Polysilicon dielectric



LAYER	PITCH	THICK	A.R.
Isolation	0.67	0.40	-
Polysilicon	0.64	0.25	-
Metal 1	0.64	0.48	1.5
Metal 2	0.93	0.90	1.9
Metal 3	0.93	0.90	1.9
Metal 4	1.60	1.33	1.7
Metal 5	2.56	1.90	1.5
	µm	µm	

Layer pitch, thickness and aspect ratio

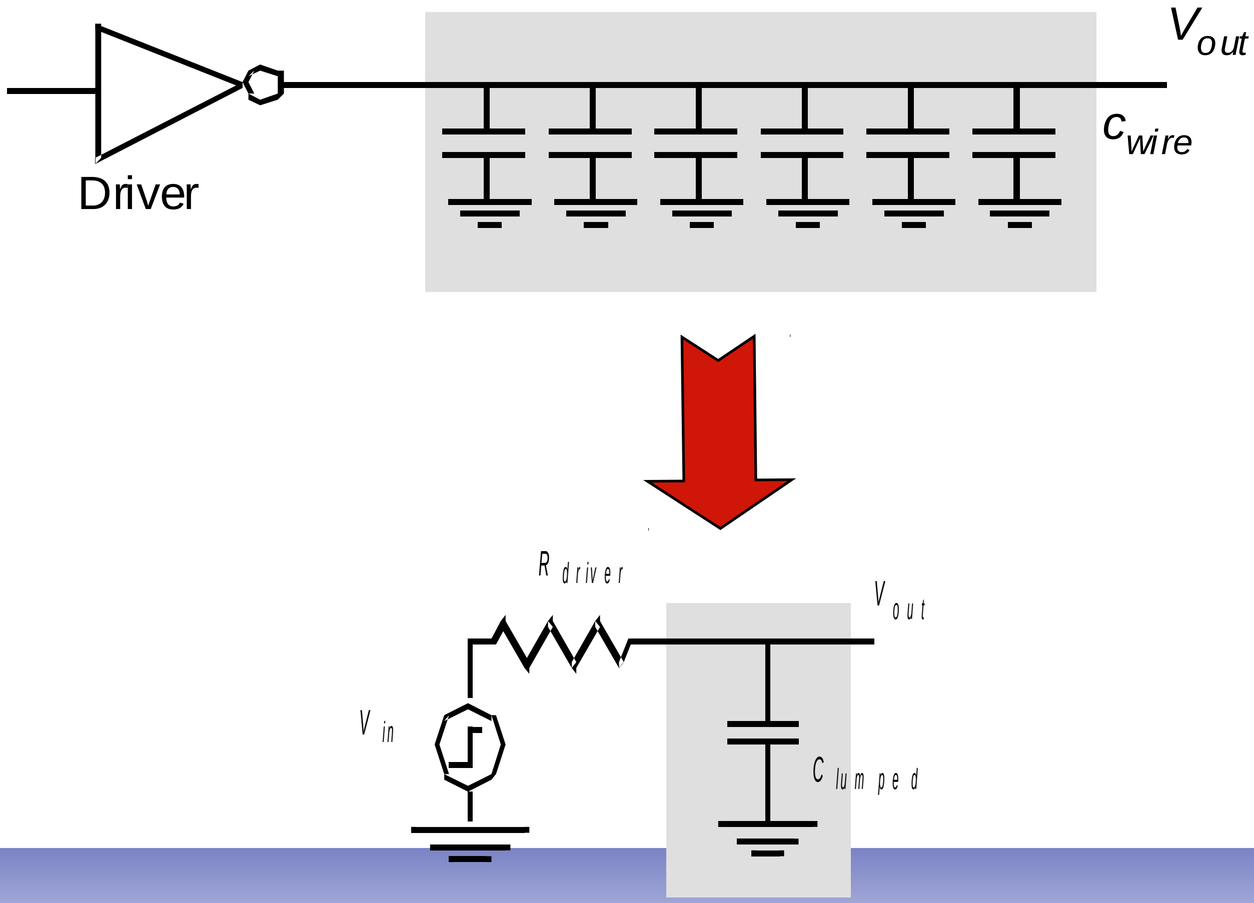


INTERCONNECT

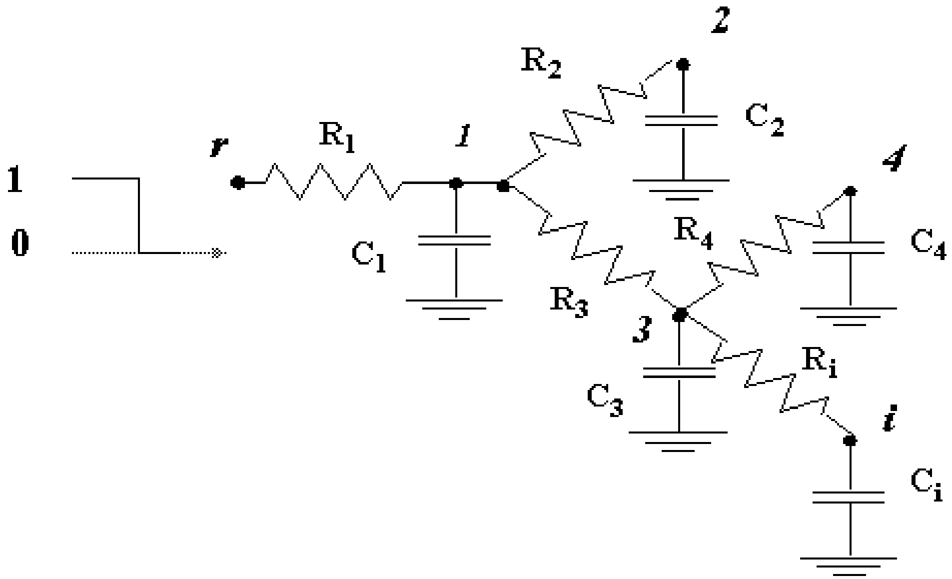
Inductance

Interconnect Modeling

The Lumped Model



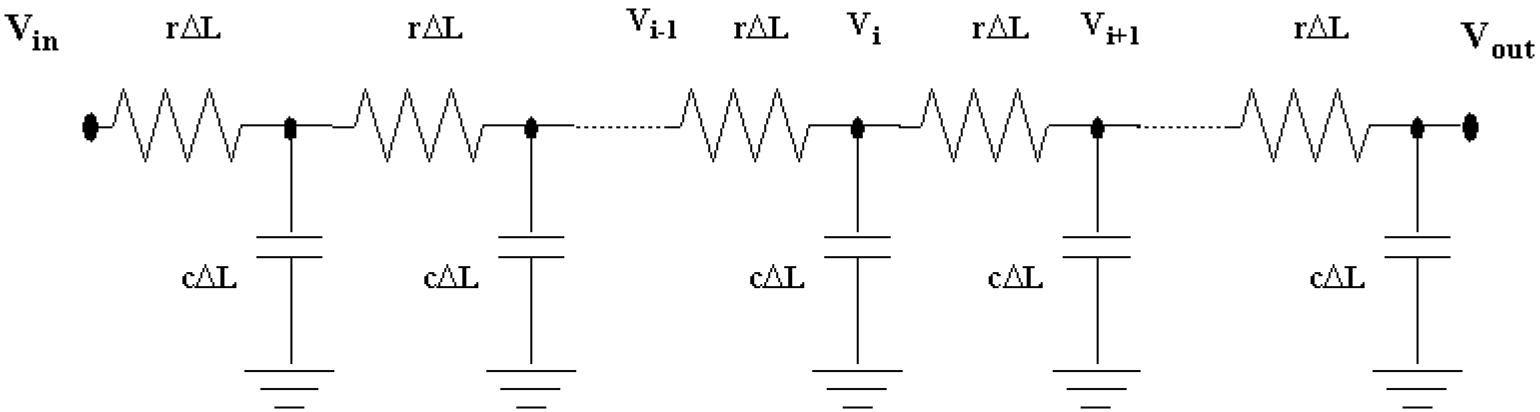
The Lumped RC-Model
The Elmore Delay



$$R_{ik} = \sum R_j \Rightarrow (R_j \in [path(s \rightarrow i) \cap path(s \rightarrow k)])$$

$$\tau_{Di} = \sum_{k=1}^{N} C_k R_{ik}$$

The Ellmore Delay
RC Chain



$$\tau_N = \sum_{i=1}^{N} R_i \sum_{j=i}^{N} C_j = \sum_{i=1}^{N} C_i \sum_{j=1}^{i} R_j$$

Wire Model

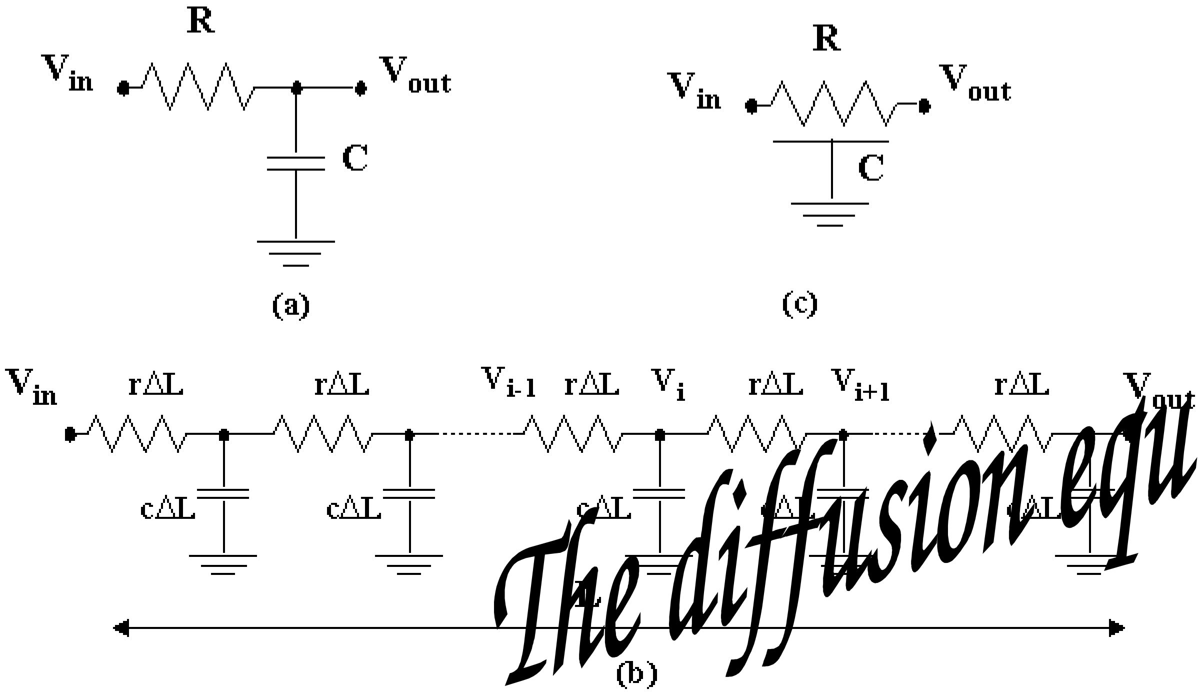
Assume: Wire modeled by N equal-length segments

$$\tau_{DN} = \left(\frac{L}{N}\right)^2 (rc + 2rc + \ldots + Nrc) = (rcL^2)\frac{N(N+1)}{2N^2} = RC\frac{N+1}{2N}$$

For large values of N:

$$\tau_{DN} = \frac{RC}{2} = \frac{rcL^2}{2}$$

The Distributed RC-line

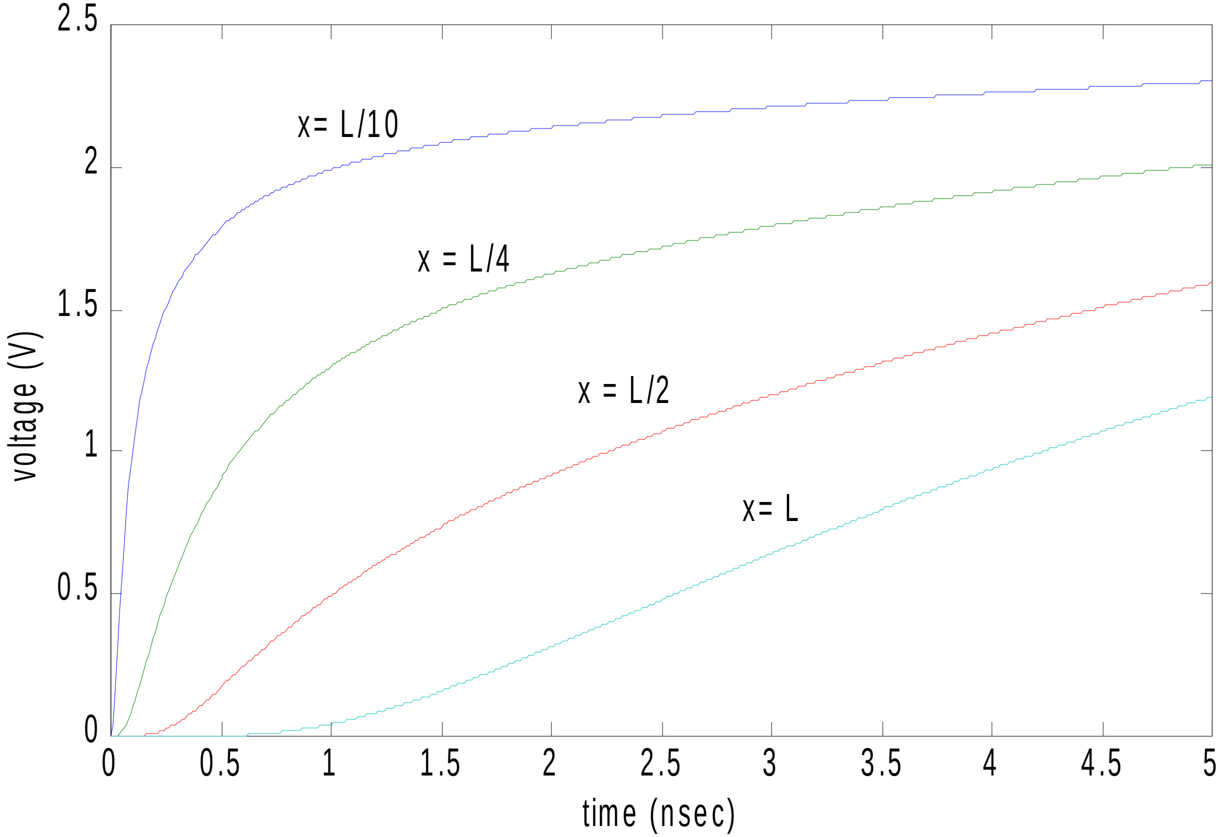


The diffusion equation

$$rc\frac{\partial V}{\partial t} = \frac{\partial^2 V}{\partial x^2}$$

$$\tau(V_{out}) = \frac{rc\,L^2}{2}$$

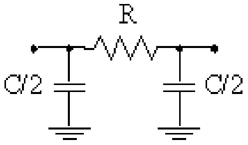
Step-response of RC wire as a function of time and space



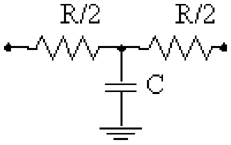
RC-Models

Voltage Range	Lumped RC-network	Distributed RC-network
0→50% (t_p)	0.69 RC	0.38 RC
0→63% (τ)	RC	0.5 RC
10%→90% (t_r)	2.2 RC	0.9 RC

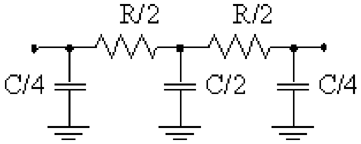
Step Response of Lumped and Distributed RC Networks: Points of Interest.



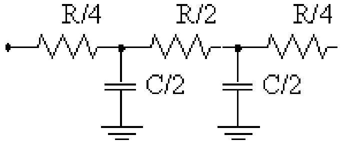
π



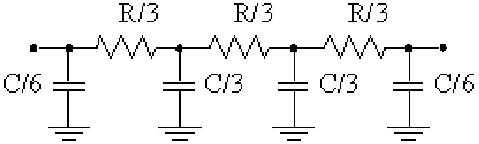
T



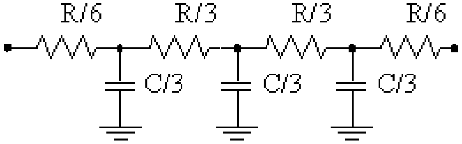
$\pi 2$



T2

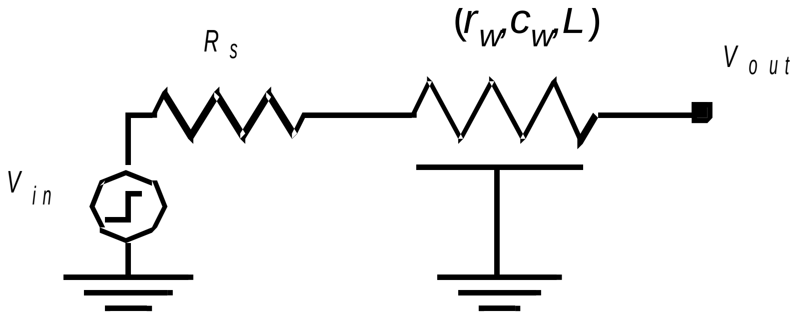


$\pi 3$



T3

Driving an RC-line



$$\tau_D = R_s C_w + \frac{R_w C_w}{2} = R_s C_w + 0.5 r_w c_w L^2$$

$$t_p = 0.69 R_s C_w + 0.38 R_w C_w$$

Design Rules of Thumb

- rc delays should only be considered when $t_{pRC} \gg t_{pgate}$ of the driving gate

$$Lcrit \gg \sqrt{t_{pgate}/0.38rc}$$

- rc delays should only be considered when the rise (fall) time at the line input is smaller than RC, the rise (fall) time of the line

$$t_{rise} < RC$$

  - when not met, the change in the signal is slower than the propagation delay of the wire